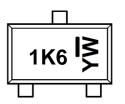
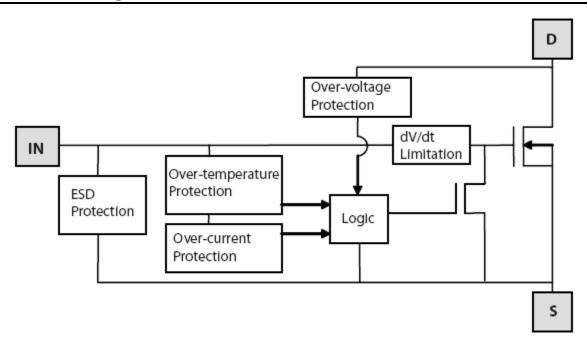


## **Marking Information**



1K6 = Product Type Marking Code Y or  $\overline{Y}$ : Year: 0 to 9 W or  $\overline{W}$ : Week: A to Z : 1 to 26 a to z: 27 to 52 z: Represents 52 & 53 Week

### **Functional Block Diagram**





# **Absolute Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Continuous Drain-Source Voltage	V <sub>DS</sub>	60	V
Drain-Source Voltage for Short Circuit Protection	V <sub>DS(SC)</sub>	36	V
Continuous Input Voltage	Vin	-0.5 +6	V
Continuous Input Current @-0.2V $\leq$ V <sub>IN</sub> $\leq$ 6V Continuous Input Current @V <sub>IN</sub> $<$ -0.2V or V <sub>IN</sub> $>$ 6V	l <sub>IN</sub>	No Limit   I <sub>IN</sub>   ≤2	mA
Pulsed Drain Current @V <sub>IN</sub> = 3.3V	IDM	2	A
Pulsed Drain Current @V <sub>IN</sub> = 5V	I <sub>DM</sub>	2.5	A
Continuous Source Current (Body Diode)	Is	1	Α
Pulsed Source Current (Body Diode)	I <sub>SM</sub>	5	Α
Unclamped Single Pulse Inductive Energy, T <sub>J</sub> = +25°C, I <sub>D</sub> = 0.5A, V <sub>DD</sub> = 24V	Eas	90	mJ
Electrostatic Discharge (Human Body Model)	V <sub>ESD</sub>	4,000	V
Charged Device Model	Vcdm	1,000	V

#### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation @T <sub>A</sub> = +25°C (Note 5) Linear Derating Factor	P <sub>D</sub>	0.83 6.66	W mW/°C
Power Dissipation @T <sub>A</sub> = +25°C (Note 6) Linear Derating Factor	PD	1.5 12.0	W mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>0JA</sub>	150	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	Reja	83	°C/W
Thermal Resistance, Junction to Case (Note 7)	Rejc	44	°C/W
Operating Temperature Range	TJ	-40 to +150	°C
Storage Temperature Range	T <sub>STG</sub>	-55 to +150	°C

## **Recommended Operating Conditions**

The ZXMS6004FFQ is optimized for use with  $\mu C$  operating from 3.3V and 5V supplies.

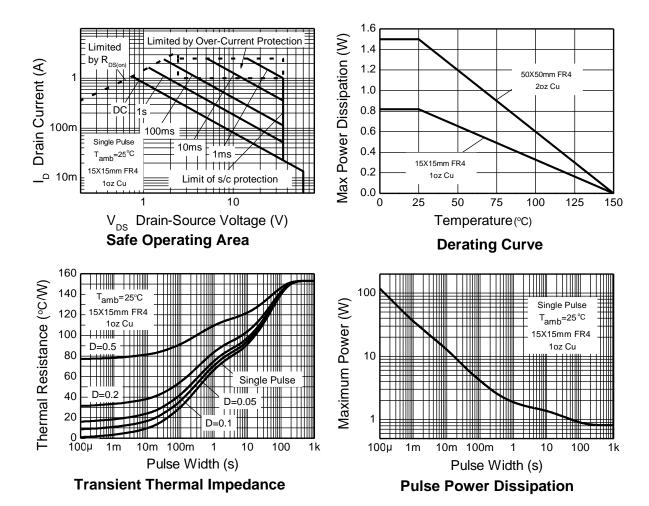
Characteristic	Symbol	Min	Max	Unit
Input Voltage Range	VIN	0	5.5	V
Ambient Temperature Range	TA	-40	+125	°C
High Level Input Voltage for MOSFET to be On	V <sub>IH</sub>	3	5.5	V
Low Level Input Voltage for MOSFET to be Off	VIL	0	0.7	V
Peripheral Supply Voltage (Voltage to Which Load is Referred)	VP	0	36	V

Notes:

- 5. For a device surface mounted on 15mm x 15mm single sided, 1oz weight copper on 1.6mm FR4 board, in still air conditions. 6. For a device surface mounted on 50mm x 50mm single sided, 2oz weight copper on 1.6mm FR4 board, in still air conditions.
- 7. Thermal resistance from junction and the mounting surfaces of the drain pins.



## **Typical Thermal Characteristics**





#### Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

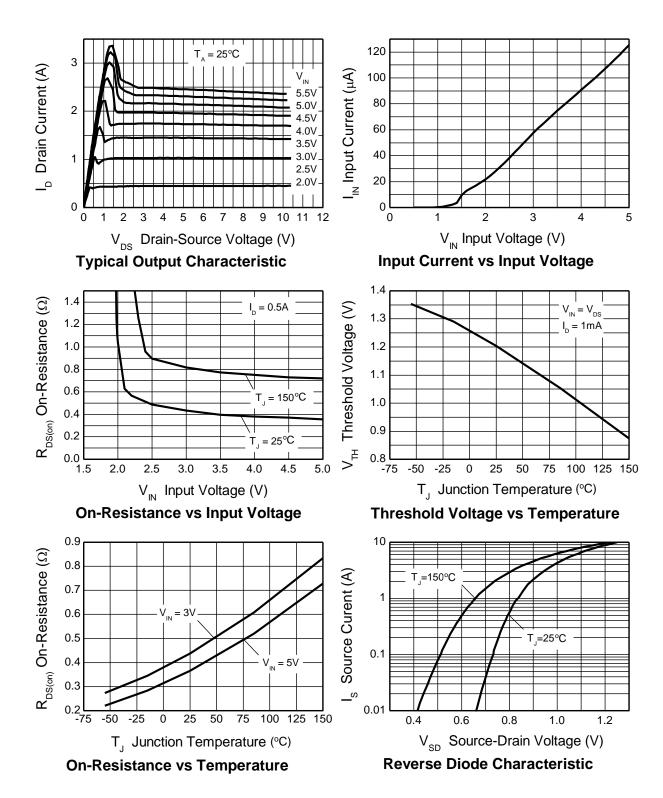
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Static Characteristics						
Drain-Source Clamp Voltage	V <sub>DS(AZ)</sub>	60	65	70	V	$I_D = 10mA$
Off-State Drain Current			_	500	nA	V <sub>DS</sub> = 12V, V <sub>IN</sub> = 0V
	IDSS	_	_	1	μΑ	$V_{DS} = 36V, V_{IN} = 0V$
Input Threshold Voltage	VIN(TH)	0.7	1	1.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 1mA
Input Current	Luci	_	60	100		$V_{IN} = +3V$
Input Current	lın	_	120	200	μΑ	$V_{IN} = +5V$
Input Current while Overtemperature Active	_	_	_	220	μΑ	V <sub>IN</sub> = +5V
Static Drain-Source On-State Resistance	Descour	_	400	600	mΩ	$V_{IN} = +3V, I_D = 0.5A$
Static Diain-Source Off-State Resistance	RDS(ON)	I	350	500	11177	$V_{IN} = +5V, I_D = 0.5A$
Continuous Prain Current (Note F)	- ID	0.9	_	_		$V_{IN} = 3V, T_A = +25^{\circ}C$
Continuous Drain Current (Note 5)		1.0	_	_	Α	V <sub>IN</sub> = 5V, T <sub>A</sub> = +25°C
Continuous Drain Current (Note 6)		1.2	_	_		$V_{IN} = 3V, T_A = +25^{\circ}C$
Continuous Diain Current (Note 6)		1.3	_	_		$V_{IN} = 5V, T_A = +25^{\circ}C$
Command Limit (Nada O)	I <sub>D(LIM)</sub>	0.7	1.7	_	Α	$V_{IN} = +3V$
Current Limit (Note 8)		1	2.2	_		$V_{IN} = +5V$
Dynamic Characteristics						
Turn-On Delay Time	t <sub>D</sub> (ON)	l	5	_		V <sub>DD</sub> = 12V, I <sub>D</sub> = 0.5A, V <sub>GS</sub> = 5V
Rise Time	t <sub>R</sub>	I	10	_		
Turn-Off Delay Time	tD(OFF)	_	45	_	μs	
Fall Time	fF	_	15	_		
Overtemperature Protection						•
Thermal Overload Trip Temperature (Note 9)	TJT	+150	+175		°C	_
Thermal Hysteresis (Note 9)	f <sub>F</sub>	_	+10	_	°C	_

Notes:

- 5. For a device surface mounted on 15mm x 15mm single sided, 1oz weight copper on 1.6mm FR4 board, in still air conditions. 6. For a device surface mounted on 50mm x 50mm single sided, 2oz weight copper on 1.6mm FR4 board, in still air conditions.
- 7. Thermal resistance from junction and the mounting surfaces of the drain pins.
- 8. The drain current is restricted only when the device is in saturation (see graph 'Typical Output Characteristic'). This allows the device to be used in the fully on-state without interference from the current limit. The device is fully protected at all drain currents, as the low power dissipation generated outside saturation makes current limit unnecessary.
- 9. Overtemperature protection is designed to prevent device destruction under fault conditions. Fault conditions are considered as "outside" normal operating range, so this part is not designed to withstand over-temperature for extended periods.

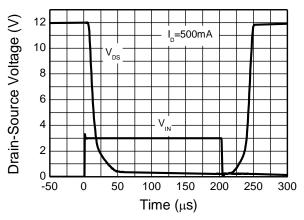


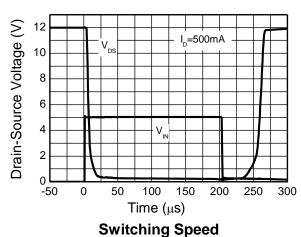
#### **Typical Performance Characteristics**





### **Typical Performance Characteristics (Continued)**





## **Switching Speed**

**Typical Short Circuit Protection** 

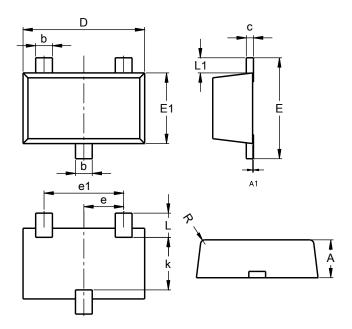
Time (ms)



### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23F

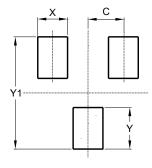


SOT23F					
Dim	Min	Max	Тур		
Α	0.80	1.00	0.90		
A1	0.00	0.10	0.01		
b	0.35	0.50	0.44		
С	0.10	0.20	0.16		
D	2.80	3.00	2.90		
е	0.95 REF				
e1	1.90 REF				
Е	2.30	2.50	2.40		
E1	1.50	1.70	1.65		
k	1.20	-	-		
L	0.30	0.65	0.50		
L1	0.30	0.50	0.40		
R	0.05	0.15	-		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23F



Dimensions	Value (in mm)			
С	0.95			
Х	0.80			
Y	1.110			
Y1	3.000			



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